

Effects of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ additions on dielectric and pyroelectric properties of Mn doped $\text{Pb}(\text{Zr}_{0.9}\text{Ti}_{0.1})\text{O}_3$ thick films

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Abstract

$\text{Pb}(\text{Zr}_{0.9}\text{Ti}_{0.1})\text{O}_3$ pyroelectric thick films adding various amounts of the sintering aids $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ have been deposited on the substrates Al_2O_3 by the screen-printing process, and the dependence of microstructure, dielectric and pyroelectric properties on the content of sintering aids has been studied. When the amount of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ increases from 0 wt% to 5.4 wt%, the sintering temperature of the thick films decreases from 1100 °C to 900 °C, and the grain size and the lattice constant decrease either, but the density and the dielectric constant increase. The $\text{Pb}(\text{Zr}_{0.9}\text{Ti}_{0.1})\text{O}_3$ thick film with 5.4 wt% of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ sintered at 900 °C has the maximum pyroelectric coefficient $10.51 \times 10^{-8} \text{ C/cm}^{-2} \text{ K}^{-1}$ and the highest figure-of-merit $10.58 \times 10^{-5} \text{ Pa}^{-0.5}$.

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1. Introduction

As the uncooled infrared detectors develop rapidly, a series of pyroelectric materials have been explored, such as lead zirconate titanate (PZT), barium strontium titanate (BST) and so on [1–3]. As far as uncooled infrared detectors are concerned, the figure-of-merit is an important parameter for assessing the quality of pyroelectric materials. In order to achieve a better response, it is necessary to increase the pyroelectric figure-of-merit $F_D = p / C_v \sqrt{\epsilon \tan \delta}$, which requires a combination of properties, namely high pyroelectric coefficient and low dielectric constant and loss [4]. Zr-rich $\text{PbZr}_{0.9}\text{Ti}_{0.1}\text{O}_3$ is a promising candidate because it has a high pyroelectric coefficient at room temperature when the transition from rhombohedral ferroelectric low temperature phase (F_{RL}) to rhombohedral ferroelectric high temperature phase (F_{RH}) takes place [5,6]. For obtaining a higher F_D , a proper amount of dopants (such as

Mn and Nb) are added to increase the pyroelectric coefficient and decrease the dielectric loss [7–10].

Recently, PZT thick films have drawn much attention because they have better electrical properties than thin films and it is unnecessary to grind or polish them like pyroelectric ceramics [11,12]. However, the processing temperatures required to obtain dense PZT ceramics are about 1200 °C, which is too high for most of substrates and incompatible with the infrared focal plane array technologies. With this end in view, reducing the sintering temperature to 900 °C is essential for the fabrication and practical application of high performance PZT thick films [13]. Several promising approaches have been explored to reduce the sintering temperature, such as addition of sintering aids, use of chemical processing, and reduction of the particle size of the starting materials [14–16]. Among them, adding sintering aids is a simple, effective and easily controllable method. Unfortunately, the general trend indicates that the electrical properties are always deteriorated when sintering aids are added [17,18].

In this work, an interesting “discrepancy” is observed from $\text{PbZr}_{0.9}\text{Ti}_{0.1}\text{O}_3$ thick films adding the sintering aids $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$. When 5.4 wt% of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ sintering

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aids are added, the sintering temperature decreases from 1100 °C to 900 °C, and meanwhile the pyroelectric coefficient and F_D increase from $1.71 \times 10^{-8} \text{ Ccm}^{-2} \text{ K}^{-1}$ and $1.56 \times 10^{-5} \text{ Pa}^{-0.5}$ to $10.51 \times 10^{-8} \text{ Ccm}^{-2} \text{ K}^{-1}$ and $10.58 \times 10^{-5} \text{ Pa}^{-0.5}$, respectively. $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ can decrease the sintering temperature and increase the density of thick films. Furthermore, Li^{1+} ions can enter into the grain lattice, increase the content of rhombohedral ferroelectric phase, and eventually increase the pyroelectric coefficient of the PZT materials [19]. As a result, the sintering aids $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ can reduce the sintering temperature and improve the pyroelectric properties, simultaneously. In this paper, the reasons for this phenomenon are discussed in details.

2. Experimental procedure

The starting materials were analytical-grade metal oxide powders: PbO (99.9%), ZrO_2 (99.6%), and TiO_2 (99.8%).

The powders were weighed according to the formula $\text{PbZr}_{0.9}\text{Ti}_{0.1}\text{O}_3$. 3.5 mol% $\text{Mn}(\text{NO}_3)_2$ solution was doped to decrease the dielectric loss, and 10 mol% excess of PbO was added to compensate the effect of lead volatilization. After that, the mixture was thoroughly milled for 4 h. The dried slurries were calcined at 850 °C for 2 h, and then ball milled again for 4 h with x wt% of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ (x is from 0 to 9) and 30 wt% of organic vehicle. The specimens with 0 wt%, 3.6 wt%, 5.4 wt%, 7.2 wt%, and 9 wt% of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ are denoted as PZT0, PZT1, PZT2, PZT3, and PZT4, respectively. Then, the films were printed on Pd/Ag coated alumina substrates. PZT0 was sintered at 1100 °C for 1 h, and PZT1, PZT2, PZT3, and PZT4 were sintered at 900 °C for 1 h. Finally, the specimens were poled at 90 °C for 1 h with the DC bias of 3 kV/mm.

The crystal structures of samples were determined by an X-ray diffractometer and the microstructures of specimens were observed by a scanning electron microscopy (SEM). The dielectric properties were measured at the frequency of

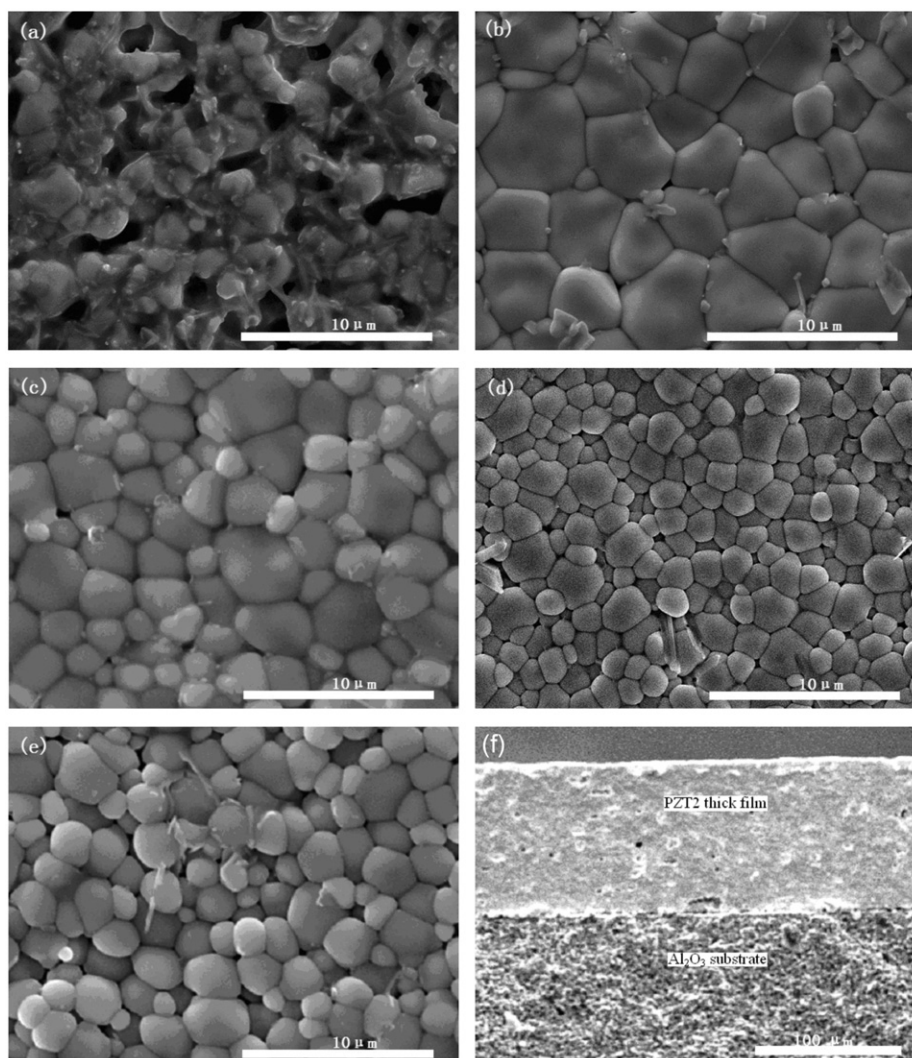


Fig. 1. Scanning electron microscopic micrographs of PZT thick films with different contents of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$: (a) 0 wt%, (b) 3.6 wt%, (c) 5.4 wt%, (d) 7.2 wt%, and (e) 9 wt%, and (f) the cross-sectional scanning electron micrographs of PZT2.

1 kHz using a LCR analyzer (HP 4192; Hewlett Packard Ltd., Palo Alto, CA), and the pyroelectric coefficient was measured by the Byer–Roundy method [20].

3. Results and discussion

The SEM micrographs of all the samples are presented in Fig. 1. From Fig. 1(a) it can be observed that the porosity of PZT0 is high even though the sintering temperature reaches up to 1100 °C and the liquid phase has been formed. For $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ added specimens that are sintered at 900 °C, the porosity decreases as the amount of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ increases when the $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ content is less than 5.4 wt%, but further increasing $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ content hinders the densification of the PZT thick films, as evidenced in Fig. 1(b–e). Fig. 1(f) is the cross section SEM picture of PZT2, it also indicates that when 5.4 wt% of sintering aids $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ are added, dense PZT thick films can be obtained at the low sintered temperature. A proper amount of sintering aids $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ usually aid the densification of thick films during sintering, but a too large amount of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ produce an initial rapid densification and leave closed pores in the ceramics that can not be removed by the solid state sintering. Moreover, the grain size decreases when the content of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ sintering aids increase, because $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ forms a liquid phase at the grain boundary or around the grain and then restrains the grain growth. The SEM micrographs indicate that $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ can optimize the microstructure of PZT thick films even at a lower sintering temperature.

Fig. 2(a) shows the X-ray diffraction patterns of all specimens. From XRD patterns it can be seen that there is only the perovskite structure in the samples. The lattice constants calculated on the basis of the least square refinement with over six peaks of diffraction patterns [21] are listed in Fig. 3. The lattice constant and unit-cell volume decrease as the content of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ increases, due to the substitution of smaller Bi^{3+} and Li^{1+} ions for larger A and B site ions [19,22,23]. It has been reported that, for PZT thick films at room temperature, the ratio of

rhombohedral phase to tetragonal phase is characterized by a (002)/(200) peak splitting near 44°, the splitting of (002) and (200) peaks indicates that the ferroelectric tetragonal and rhombohedral phases coexist in the PZT, and the proportion of rhombohedral phase increases while the peak splitting effect is weakening. The enlarged pictures of the typical peaks when 2θ is about 44° are shown in Fig. 2(b). The splitting of (002) and (200) peaks can be seen in PZT0. As the amount of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ increases, the split peaks gradually merge into one peak. This means that the proportion of rhombohedral phase in PZT increases as the content of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ increases. The result is consistent with the investigation performed by Gao who attributed the increase of the rhombohedral phase content to the substitution of Li^{1+} ions for B site ions [19]. The high pyroelectric coefficient of Zr-rich PZT materials comes from the rhombohedral ferroelectric $F_{\text{RL}}\text{--}F_{\text{RH}}$ phase transition; therefore, the proportion of rhombohedral phase is crucial [5,6]. The PZT thick films containing sintering aids $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ have a higher content of rhombohedral phase, which indicates that the higher pyroelectric coefficient can be expected.

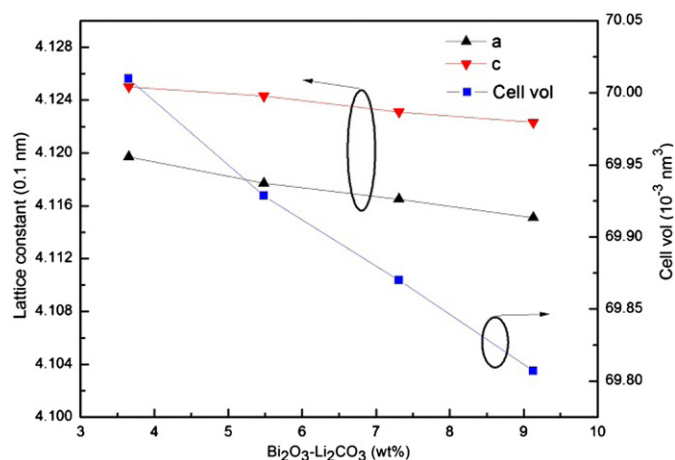


Fig. 3. The lattice constant and unit-cell volume of PZT thick films with different contents of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$.

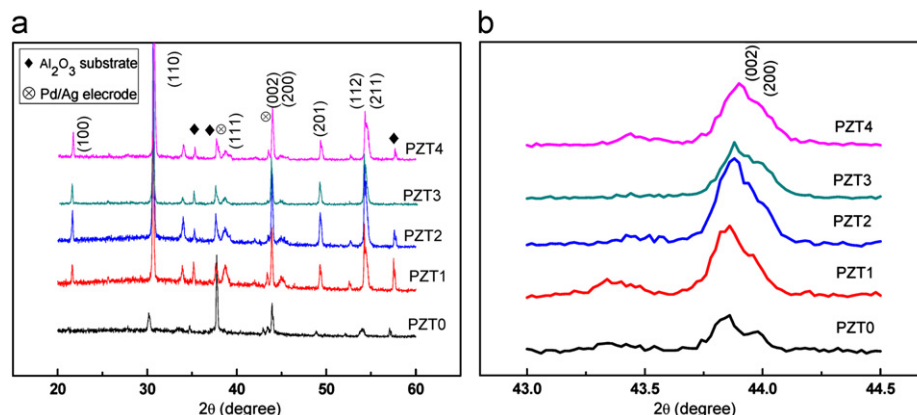


Fig. 2. (a) X-ray diffraction patterns and (b) the enlarged picture around $2\theta=44^\circ$ of PZT thick films with different contents of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$.

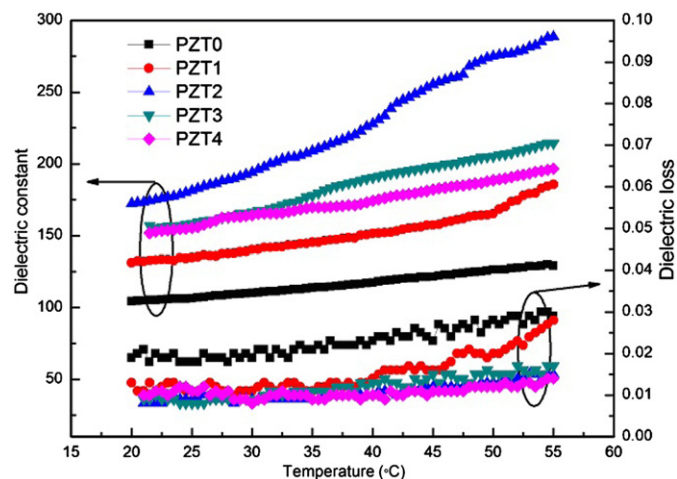


Fig. 4. Temperature dependence of dielectric constant and loss of PZT thick films with different contents of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$.

The temperature-dependent dielectric constant and loss curves of the PZT thick films with various contents of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ are shown in Fig. 4. The dielectric constant increases when the content of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ increase from 0 wt% to 5.4 wt%, but then decreases as the content of the sintering aids increase to 9 wt%. PZT0 has the lowest dielectric constant due to its high porosity. The density of PZT thick films increases as the $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ content increases, resulting in the increase of the dielectric constant of PZT1 and PZT2. On the other hand, the internal stress between the grains increases as the grain size decreases. When the grain size is larger than $0.8\text{ }\mu\text{m}$, the content of 90° domain increases as the internal stress increases, and this leads to the increase of dielectric constant. [24] The grain size of PZT thick films decreases as the $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ content increases, and this also results in the increase of the dielectric constant. However, when the content of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ is more than 5.4 wt%, the grain size decreases and the proportion of grain boundary increases dramatically, as evidenced in Fig. 1. The dielectric constant of grain boundary is much lower than that of grains, and hence the dielectric constant of the PZT thick films decreases with the further increase of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ [25,26]. The phenomenon that PZT0 shows the highest dielectric loss can also be attributed to its low density. Because of their high densities, samples sintered at 900°C with 5.4 wt% or more $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ have low dielectric losses, which are favorable to the increase of the pyroelectric figure-of-merit.

Fig. 5(a) shows the curves of pyroelectric coefficient versus temperature of samples with different contents of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$. The thick films sintered at 1100°C without adding the sintering aids $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ show a low pyroelectric coefficient on account of its high porosity and low content of rhombohedral phase. The pyroelectric coefficient increases dramatically. A steep pyroelectric coefficient peak can be observed as the $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$

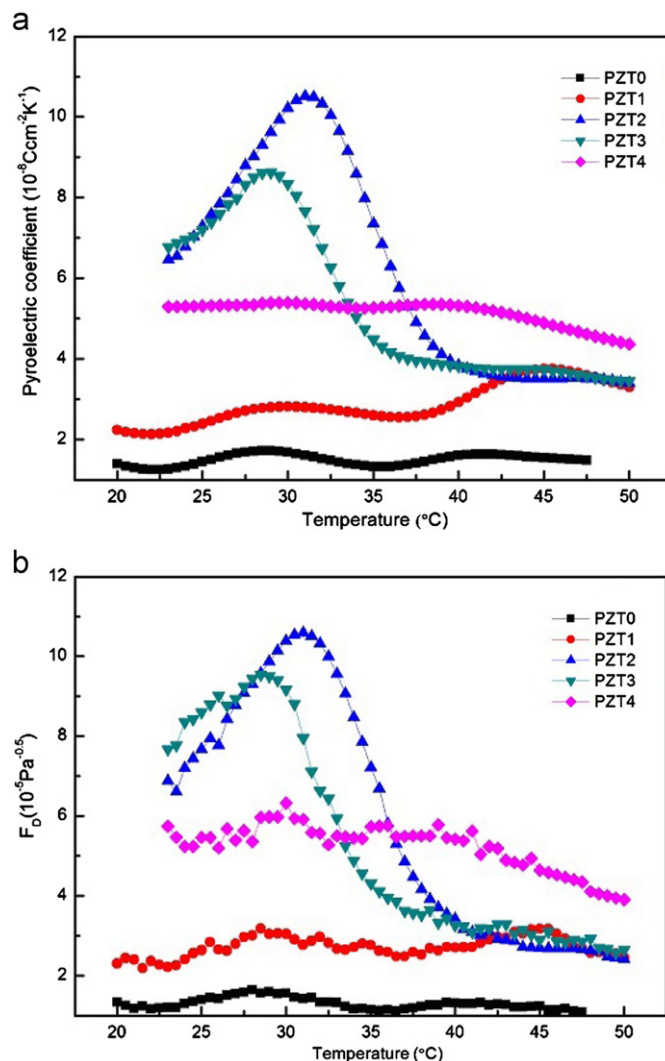


Fig. 5. Temperature dependence of (a) pyroelectric coefficient and (b) pyroelectric figure-of-merit.

content increases to 5.4 wt%. There are two reasons for the obvious increase of the pyroelectric coefficient of PZT2. Firstly, an appropriate amount of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ as sintering aid can decrease the porosity and increase the density of the PZT thick films, and finally increase the pyroelectric coefficient. Secondly, for Zr-rich PZT, the $F_{\text{RL}}\text{--}F_{\text{HL}}$ phase transition occurs when the temperature varies near 30°C . It is well known that the high pyroelectric coefficient can be obtained when the rhombohedral ferroelectric $F_{\text{RL}}\text{--}F_{\text{RH}}$ phase transition occurs [5,6], and therefore the Zr-rich PZT samples with the large proportion of rhombohedral phase can exhibit a high pyroelectric coefficient. Thick films adding 5.4 wt% of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ have a greater proportion of rhombohedral phase owing to the substitution of Li^{1+} ions for B site ions, as evidenced by the XRD pattern. Consequently, it shows a steep pyroelectric coefficient peak. This result reveals that the $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ sintering aids can not only reduce the sintering temperature and increase the density, but also

lead to the increase of pyroelectric coefficient by 6 times. When the content of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ increases to 9 wt%, the pyroelectric coefficient decreases and the pyroelectric coefficient peak is suppressed. When the grain size decreases, the internal stresses among the grains increase. The large internal stresses can increase the dispersity of the $F_{R(\text{LT})}\text{--}F_{R(\text{HT})}$ phase transition and suppress the pyroelectric coefficient peak [27]. Also, the grain boundary content increases as the grain size decreases, and the high content of non-ferroelectric grain boundary results in the decrease of pyroelectric coefficient.

Fig. 5(b) exhibits the figure-of-merit F_D of all samples. PZT2 has the largest pyroelectric coefficient and a low dielectric loss, and therefore it shows the highest F_D of $10.58 \times 10^{-5} \text{ Pa}^{-0.5}$, which is about 7 times as that of PZT thick films without adding $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$.

4. Conclusions

The effects of the sintering aids $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ on the microstructure, dielectric and pyroelectric properties of PZT thick films have been systematically investigated. The results indicate that unlike other sintering aids, a proper amount of $\text{Bi}_2\text{O}_3\text{--Li}_2\text{CO}_3$ can reduce the sintering temperature from 1100 °C to 900 °C, decrease the porosity of the PZT thick films, and lead to more-than-6-times increase of the pyroelectric coefficient and figure-of-merit, simultaneously.

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